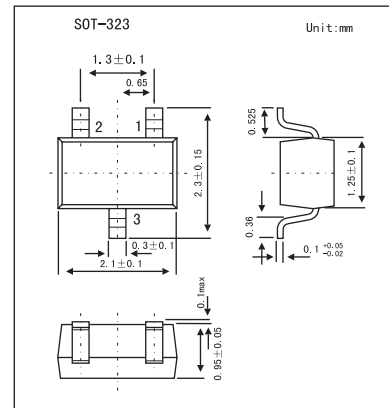


## Silicon Schottky Barrier Diode

## HSB276AS

## ■ Features

- High forward current, Low capacitance.
- HSB276AS which is interconnected in series configuration is designed for balanced mixer use.
- CMPAK package is suitable for high density surface mounting and high speed assembly.



## ■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Value	Unit
Repetitive peak reverse voltage	$V_{RRM}$	5	V
Reverse voltage	$V_R$	3	V
Average rectified current	$I_o$	30	mA
Junction temperature	$T_j$	125	°C
Storage temperature	$T_{stg}$	-55 to +125	°C

## ■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Forward voltage	$V_F$	$I_F = 1.0 \text{ mA}$	3			V
Reverse current	$I_R$	$V_R = 0.5 \text{ V}$			50	$\mu\text{A}$
Forward current	$I_F$	$V_F = 0.5 \text{ V}$	35			mA
Capacitance	$C$	$V_R = 0.5 \text{ V}, f = 1 \text{ MHz}$			0.90	pF
Capacitance deviation	$\Delta C$	$V_R = 0.5 \text{ V}, f = 1 \text{ MHz}$			0.10	pF
ESD-Capability (Note 1)		$C=200\text{pF}, R=0\ \Omega$ Both forward and reverse direction 1 pulse.	30			V

Note

1. Failure criterion ;  $I_R \geq 100 \mu\text{A}$  at  $V_R = 0.5 \text{ V}$ 

## ■ Marking

Marking	E8
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